

ABSTRACT OF THE DISCLOSURE

A reflective mask blank for EUV lithography includes a substrate; a multilayer
5 reflective film that reflects EUV light; a protection film that protects the multilayer reflective film; and an absorption film that absorbs the EUV light, in this order from bottom to top. The protection film includes an upper layer made of
10 a rhodium-based material containing Rh, or containing Rh and at least one element selected from a group consisting of N, O, C, B, Ru, Nb, Mo, Ta, Ir, Pd, Zr, and Ti; and a lower layer satisfying a condition $k < -0.15n + 0.16$ in an EUV region [in the
15 formula n represents a refractive index and k represents an extinction coefficient].